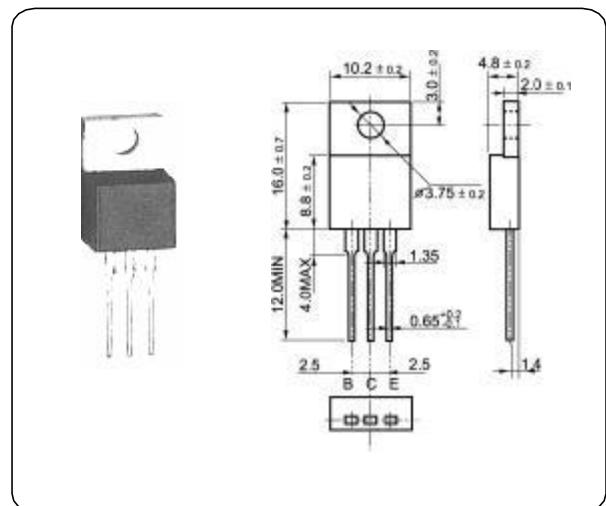


GENERAL DESCRIPTION

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

Parameter	Symbol	Typ	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	600	V
RMS on-state current	$I_{T(RMS)}$	8.0	A
Non-repetitive peak on-state current	I_{TSM}	65	A
Max. Operating Junction Temperature	T_J	110	°C
Storage Temperature	T_{stg}	-45~150	°C



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}		—	600	—	V
RMS on-state current	$I_{T(RMS)}$	full sine wave; $T_{mb} \leq 107$ °C	—	8	—	A
On-state voltage	V_T	$I_T = 10$ A	—	1.4	1.7	V
Holding current	I_H	$V_D = 12$ V; $I_{GT} = 0.1$ A	—	2.2	15	mA
Gate trigger current	T2+G+	$V_D = 12$ V; $I_T = 0.1$ A	—	2.5	10	mA
	T2+G-		—	4.0	10	
	T2-G-		—	5.0	10	
	T2-G+		—	11	25	
Latching current	T2+G+	$V_D = 12$ V; $I_{GT} = 0.1$ A	—	3.0	15	mA
	T2+G-		—	10	20	
	T2-G-		—	2.5	15	
	T2-G+		—	4.0	20	
Gate trigger voltage	V_{GT}	$V_D = 12$ V; $I_T = 0.1$ A	—	0.7	1.5	V